

ABSTRACT

A semiconductor device comprising: a MIS type field effect transistor which comprises a semiconductor raised portion protruding from a substrate plane, a gate electrode extending over the semiconductor raised portion from the top onto the opposite side faces of the semiconductor raised portion, a
5 gate insulation film existing between the gate electrode and the semiconductor raised portion, and source and drain regions provided in the semiconductor raised portion; an interlayer insulating film provided on a substrate including the transistor; and a buried conductor interconnect that is
10 formed by filling in a trench formed in the interlayer insulating film with a conductor, wherein the buried conductor interconnect connects one of the source and drain regions of the semiconductor raised portion and another conductive portion below the interlayer insulating film.